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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, DCMI, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f407zgt7

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2 Description

The STM32F405xx and STM32F407xx family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core operating at a frequency of up to 168 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F405xx and STM32F407xx family incorporates high-speed embedded memories (Flash memory up to 1 Mbyte, up to 192 Kbytes of SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers, a true random number generator (RNG). They also feature standard and advanced communication interfaces.

- Up to three I²Cs
- Three SPIs, two I²Ss full duplex. To achieve audio class accuracy, the I2S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus two UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- An SDIO/MMC interface
- Ethernet and the camera interface available on STM32F407xx devices only.

New advanced peripherals include an SDIO, an enhanced flexible static memory control (FSMC) interface (for devices offered in packages of 100 pins and more), a camera interface for CMOS sensors. Refer to [Table 2: STM32F405xx and STM32F407xx: features and peripheral counts](#) for the list of peripherals available on each part number.

The STM32F405xx and STM32F407xx family operates in the –40 to +105 °C temperature range from a 1.8 to 3.6 V power supply. The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor: refer to [Section : Internal reset OFF](#). A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F405xx and STM32F407xx family offers devices in various packages ranging from 64 pins to 176 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F405xx and STM32F407xx microcontroller family suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances

2.2.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

2.2.6 Embedded SRAM

All STM32F40xxx products embed:

- Up to 192 Kbytes of system SRAM including 64 Kbytes of CCM (core coupled memory) data RAM
RAM memory is accessed (read/write) at CPU clock speed with 0 wait states.
- 4 Kbytes of backup SRAM
This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

2.2.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS) and the slaves (Flash memory, RAM, FSMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Table 4. Timer feature comparison (continued)

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary output	Max interface clock (MHz)	Max timer clock (MHz)
General purpose	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	42	84
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	42	84
	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	84	168
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	84	168
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	42	84
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	42	84
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	42	84

Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 and TIM8 support independent DMA request generation.

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

2.2.38 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

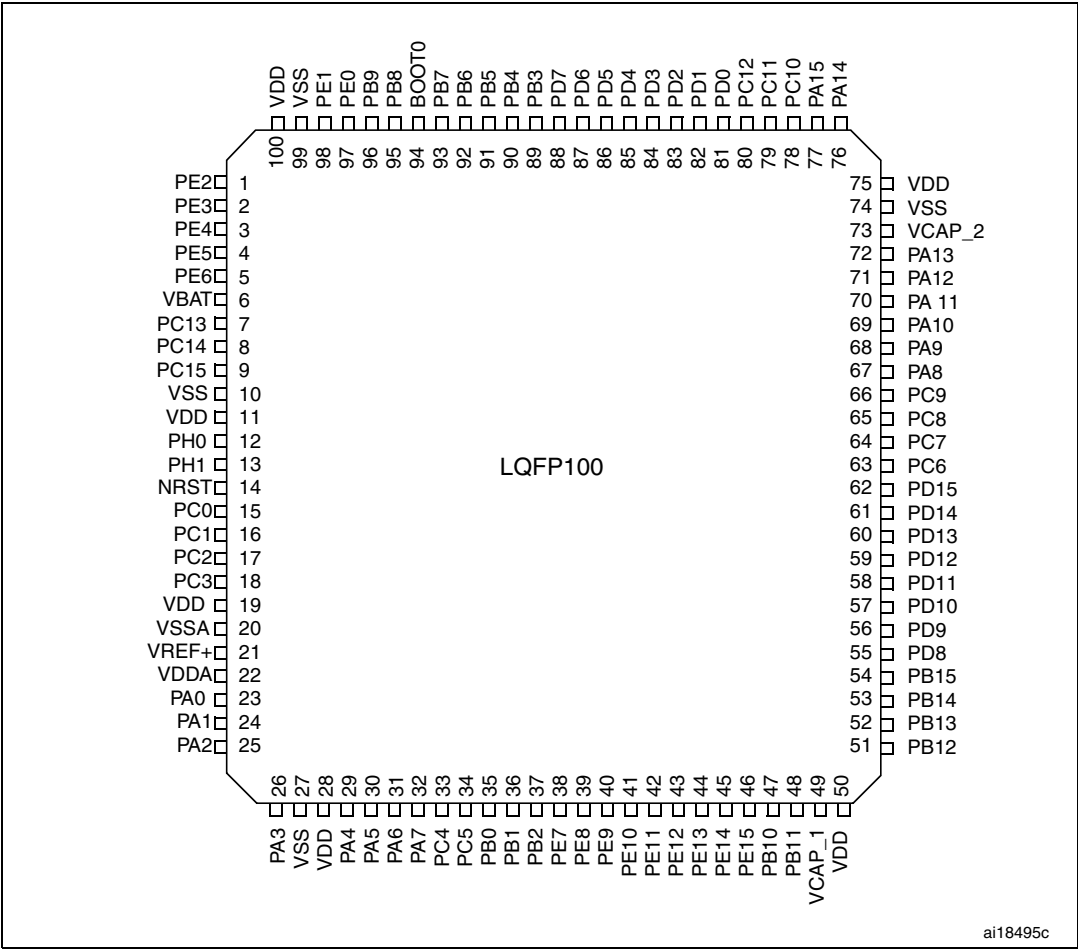
Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

2.2.39 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F40xxx through a small number of ETM pins to an external hardware trace port analyser (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

Figure 13. STM32F40xxx LQFP100 pinout



1. The above figure shows the package top view.

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	-	-	49	R6	59	PF11	I/O	FT	-	DCMI_D12/ EVENTOUT	-
-	-	-	50	P6	60	PF12	I/O	FT	-	FSMC_A6/ EVENTOUT	-
-	-	-	51	M8	61	V _{SS}	S	-	-	-	-
-	-	-	52	N8	62	V _{DD}	S	-	-	-	-
-	-	-	53	N6	63	PF13	I/O	FT	-	FSMC_A7/ EVENTOUT	-
-	-	-	54	R7	64	PF14	I/O	FT	-	FSMC_A8/ EVENTOUT	-
-	-	-	55	P7	65	PF15	I/O	FT	-	FSMC_A9/ EVENTOUT	-
-	-	-	56	N7	66	PG0	I/O	FT	-	FSMC_A10/ EVENTOUT	-
-	-	-	57	M7	67	PG1	I/O	FT	-	FSMC_A11/ EVENTOUT	-
-	G6	38	58	R8	68	PE7	I/O	FT	-	FSMC_D4/TIM1_ETR/ EVENTOUT	-
-	H6	39	59	P8	69	PE8	I/O	FT	-	FSMC_D5/ TIM1_CH1N/ EVENTOUT	-
-	J6	40	60	P9	70	PE9	I/O	FT	-	FSMC_D6/TIM1_CH1/ EVENTOUT	-
-	-	-	61	M9	71	V _{SS}	S	-	-	-	-
-	-	-	62	N9	72	V _{DD}	S	-	-	-	-
-	F6	41	63	R9	73	PE10	I/O	FT	-	FSMC_D7/TIM1_CH2N/ EVENTOUT	-
-	J5	42	64	P10	74	PE11	I/O	FT	-	FSMC_D8/TIM1_CH2/ EVENTOUT	-
-	H5	43	65	R10	75	PE12	I/O	FT	-	FSMC_D9/TIM1_CH3N/ EVENTOUT	-
-	G5	44	66	N11	76	PE13	I/O	FT	-	FSMC_D10/TIM1_CH3/ EVENTOUT	-
-	F5	45	67	P11	77	PE14	I/O	FT	-	FSMC_D11/TIM1_CH4/ EVENTOUT	-
-	G4	46	68	R11	78	PE15	I/O	FT	-	FSMC_D12/TIM1_BKIN/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
29	H4	47	69	R12	79	PB10	I/O	FT	-	SPI2_SCK / I2S2_CK / I2C2_SCL/ USART3_TX / OTG_HS_ULPI_D3 / ETH_MII_RX_ER / TIM2_CH3/ EVENTOUT	-
30	J4	48	70	R13	80	PB11	I/O	FT	-	I2C2_SDA/USART3_RX/ OTG_HS_ULPI_D4 / ETH_RMII_TX_EN/ ETH_MII_TX_EN / TIM2_CH4/ EVENTOUT	-
31	F4	49	71	M10	81	V _{CAP_1}	S		-	-	-
32	-	50	72	N10	82	V _{DD}	S		-	-	-
-	-	-	-	M11	83	PH6	I/O	FT	-	I2C2_SMBA / TIM12_CH1 / ETH_MII_RXD2/ EVENTOUT	-
-	-	-	-	N12	84	PH7	I/O	FT	-	I2C3_SCL / ETH_MII_RXD3/ EVENTOUT	-
-	-	-	-	M12	85	PH8	I/O	FT	-	I2C3_SDA / DCMI_HSYNC/ EVENTOUT	-
-	-	-	-	M13	86	PH9	I/O	FT	-	I2C3_SMBA / TIM12_CH2/ DCMI_D0/ EVENTOUT	-
-	-	-	-	L13	87	PH10	I/O	FT	-	TIM5_CH1 / DCMI_D1/ EVENTOUT	-
-	-	-	-	L12	88	PH11	I/O	FT	-	TIM5_CH2 / DCMI_D2/ EVENTOUT	-
-	-	-	-	K12	89	PH12	I/O	FT	-	TIM5_CH3 / DCMI_D3/ EVENTOUT	-
-	-	-	-	H12	90	V _{SS}	S	-	-	-	-
-	-	-	-	J12	91	V _{DD}	S	-	-	-	-

Table 7. STM32F40xxx pin and ball definitions (continued)

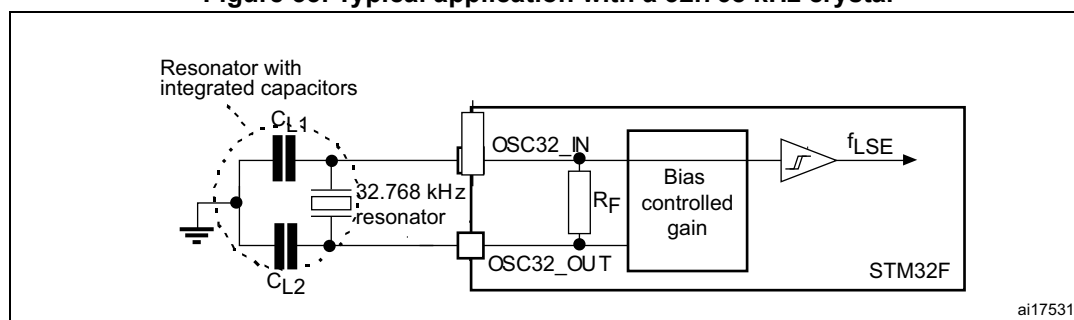
Pin number						Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	A8	-	143	C6	171	PDR_ON	I	FT	-	-	-
64	A1	100	144	C5	172	V _{DD}	S	-	-	-	-
-	-	-	-	D4	173	PI4	I/O	FT	-	TIM8_BKIN / DCMI_D5/ EVENTOUT	-
-	-	-	-	C4	174	PI5	I/O	FT	-	TIM8_CH1 / DCMI_VSYNC/ EVENTOUT	-
-	-	-	-	C3	175	PI6	I/O	FT	-	TIM8_CH2 / DCMI_D6/ EVENTOUT	-
-	-	-	-	C2	176	PI7	I/O	FT	-	TIM8_CH3 / DCMI_D7/ EVENTOUT	-

- Function availability depends on the chosen device.
- PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:
 - The speed should not exceed 2 MHz with a maximum load of 30 pF.
 - These I/Os must not be used as a current source (e.g. to drive an LED).
- Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: www.st.com.
- FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
- If the device is delivered in an UFBGA176 or WLCSP90 and the BYPASS_REG pin is set to VDD (Regulator off/internal reset ON mode), then PA0 is used as an internal Reset (active low).

Table 8. FSMC pin definition

Pins ⁽¹⁾	FSMC				LQFP100 ⁽²⁾	WLCSP90 ⁽²⁾
	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit		
PE2	-	A23	A23	-	Yes	-
PE3	-	A19	A19	-	Yes	-
PE4	-	A20	A20	-	Yes	-
PE5	-	A21	A21	-	Yes	-
PE6	-	A22	A22	-	Yes	-
PF0	A0	A0	-	-	-	-

Figure 33. Typical application with a 32.768 kHz crystal



5.3.9 Internal clock source characteristics

The parameters given in [Table 34](#) and [Table 35](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

High-speed internal (HSI) RC oscillator

Table 34. HSI oscillator characteristics ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user trimming step ⁽²⁾	-	-	-	1	%
	Accuracy of the HSI oscillator	$T_A = -40$ to $105\text{ }^{\circ}\text{C}^{(3)}$	-8	-	4.5	%
		$T_A = -10$ to $85\text{ }^{\circ}\text{C}^{(3)}$	-4	-	4	%
		$T_A = 25\text{ }^{\circ}\text{C}^{(4)}$	-1	-	1	%
$t_{su(HSI)}^{(2)}$	HSI oscillator startup time	-	-	2.2	4	μs
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption	-	-	60	80	μA

1. $V_{DD} = 3.3\text{ V}$, $T_A = -40$ to $105\text{ }^{\circ}\text{C}$ unless otherwise specified.

2. Guaranteed by design.

3. Guaranteed by characterization.

4. Factory calibrated, parts not soldered.

Low-speed internal (LSI) RC oscillator

Table 35. LSI oscillator characteristics ⁽¹⁾

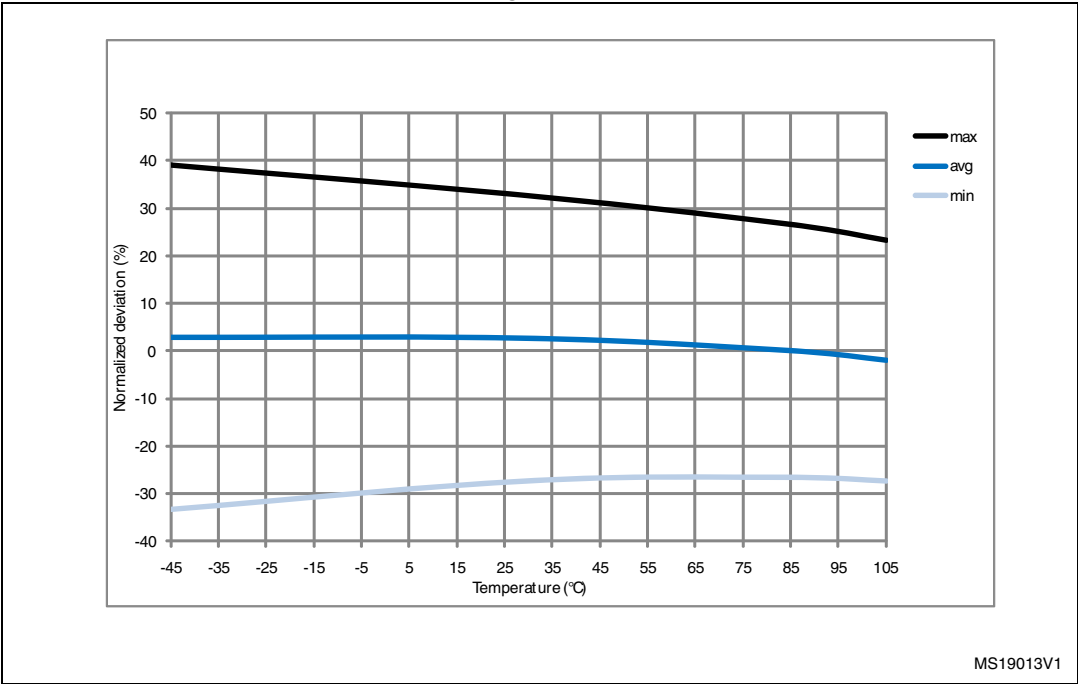
Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(2)}$	Frequency	17	32	47	kHz
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	15	40	μs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	0.4	0.6	μA

1. $V_{DD} = 3\text{ V}$, $T_A = -40$ to $105\text{ }^{\circ}\text{C}$ unless otherwise specified.

2. Guaranteed by characterization.

3. Guaranteed by design.

Figure 34. ACC_{LSI} versus temperature



MS19013V1

5.3.10 PLL characteristics

The parameters given in [Table 36](#) and [Table 37](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 36. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock ⁽¹⁾	-	0.95 ⁽²⁾	1	2.10	MHz
f_{PLL_OUT}	PLL multiplier output clock	-	24	-	168	MHz
f_{PLL48_OUT}	48 MHz PLL multiplier output clock	-	-	48	75	MHz
f_{VCO_OUT}	PLL VCO output	-	100	-	432	MHz
t_{LOCK}	PLL lock time	VCO freq = 100 MHz	75	-	200	μs
		VCO freq = 432 MHz	100	-	300	

Table 41. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t_{prog}	Double word programming	$T_A = 0 \text{ to } +40 \text{ }^\circ\text{C}$ $V_{DD} = 3.3 \text{ V}$ $V_{PP} = 8.5 \text{ V}$	-	16	100 ⁽²⁾	μs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	6.9	-	s
V_{prog}	Programming voltage	-	2.7	-	3.6	V
V_{PP}	V_{PP} voltage range	-	7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin	-	10	-	-	mA
$t_{VPP}^{(3)}$	Cumulative time during which V_{PP} is applied	-	-	-	1	hour

1. Guaranteed by design.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 42. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N_{END}	Endurance	$T_A = -40 \text{ to } +85 \text{ }^\circ\text{C}$ (6 suffix versions) $T_A = -40 \text{ to } +105 \text{ }^\circ\text{C}$ (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle ⁽²⁾ at $T_A = 85 \text{ }^\circ\text{C}$	30	Years
		1 kcycle ⁽²⁾ at $T_A = 105 \text{ }^\circ\text{C}$	10	
		10 kcycles ⁽²⁾ at $T_A = 55 \text{ }^\circ\text{C}$	20	

1. Guaranteed by characterization.
2. Cycling performed over the whole temperature range.

5.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB:** A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC² code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 44. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{CPU}]	Unit
				25/168 MHz	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running from Flash with ART accelerator enabled	0.1 to 30 MHz	32	dBμV
			30 to 130 MHz	25	
			130 MHz to 1GHz	29	
			SAE EMI Level	4	-
		V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running from Flash with ART accelerator and PLL spread spectrum enabled	0.1 to 30 MHz	19	dBμV
			30 to 130 MHz	16	
			130 MHz to 1GHz	18	
			SAE EMI level	3.5	-

5.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 45. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C conforming to JESD22-A114	2	2000 ⁽²⁾	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C conforming to ANSI/ESD STM5.3.1	II	500	

1. Guaranteed by characterization.

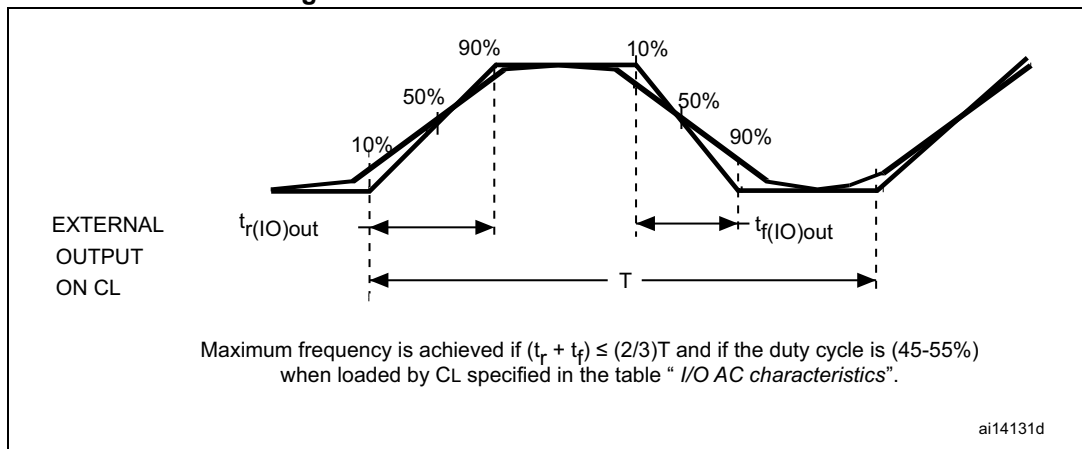
2. On V_{BAT} pin, V_{ESD(HBM)} is limited to 1000 V.

Table 50. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	100 ⁽⁴⁾	MHz
			$C_L = 30 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	50 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	180 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	100 ⁽⁴⁾	
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 30 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	4	ns
			$C_L = 30 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	6	
			$C_L = 10 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	2.5	
			$C_L = 10 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	4	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

1. Guaranteed by characterization.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in [Figure 37](#).
4. For maximum frequencies above 50 MHz, the compensation cell should be used.

Figure 37. I/O AC characteristics definition



SPI interface characteristics

Unless otherwise specified, the parameters given in [Table 55](#) for SPI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 14](#) with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30\text{ pF}$
- Measurement points are done at CMOS levels: $0.5 V_{DD}$

Refer to [Section 5.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 55. SPI dynamic characteristics⁽¹⁾

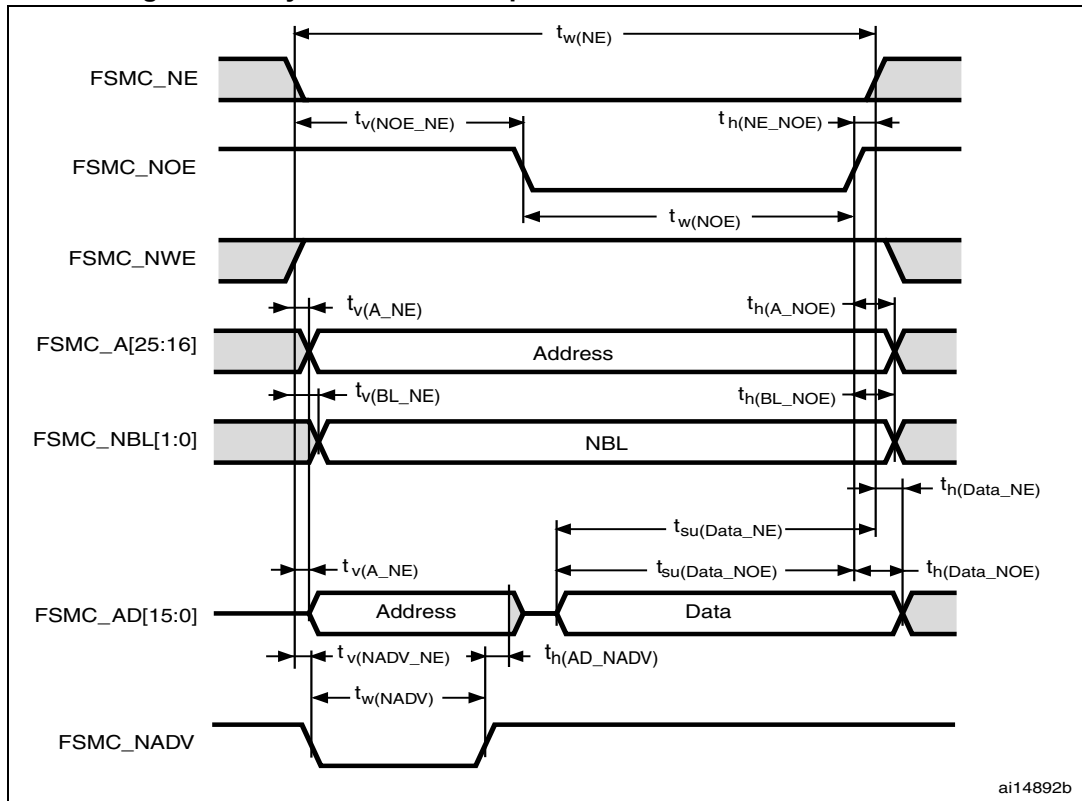
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{SCK}	SPI clock frequency	Master mode, SPI1, 2.7V < V _{DD} < 3.6V	-	-	42	MHz
		Slave mode, SPI1, 2.7V < V _{DD} < 3.6V			42	
1/t _{c(SCK)}		Master mode, SPI1/2/3, 1.7V < V _{DD} < 3.6V	-	-	21	
		Slave mode, SPI1/2/3, 1.7V < V _{DD} < 3.6V			21	
Duty(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%

Table 67. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{lat}^{(4)}$	Injection trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.100	μs
			-	-	$3^{(7)}$	$1/f_{ADC}$
$t_{latr}^{(4)}$	Regular trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.067	μs
			-	-	$2^{(7)}$	$1/f_{ADC}$
$t_S^{(4)}$	Sampling time	$f_{ADC} = 30\text{ MHz}$	0.100	-	16	μs
		-	3	-	480	$1/f_{ADC}$
$t_{STAB}^{(4)}$	Power-up time	-	-	2	3	μs
$t_{CONV}^{(4)}$	Total conversion time (including sampling time)	$f_{ADC} = 30\text{ MHz}$ 12-bit resolution	0.50	-	16.40	μs
		$f_{ADC} = 30\text{ MHz}$ 10-bit resolution	0.43	-	16.34	μs
		$f_{ADC} = 30\text{ MHz}$ 8-bit resolution	0.37	-	16.27	μs
		$f_{ADC} = 30\text{ MHz}$ 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t_S for sampling + n-bit resolution for successive approximation)				$1/f_{ADC}$
$f_S^{(4)}$	Sampling rate ($f_{ADC} = 30\text{ MHz}$, and $t_S = 3\text{ ADC cycles}$)	12-bit resolution Single ADC	-	-	2	Msp/s
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msp/s
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msp/s
$I_{VREF+}^{(4)}$	ADC V_{REF} DC current consumption in conversion mode	-	-	300	500	μA
$I_{VDPA}^{(4)}$	ADC V_{DDA} DC current consumption in conversion mode	-	-	1.6	1.8	mA

- V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to [Section : Internal reset OFF](#)).
- It is recommended to maintain the voltage difference between V_{REF+} and V_{DDA} below 1.8 V.
- $V_{DDA} - V_{REF+} < 1.2\text{ V}$.
- Guaranteed by characterization.
- V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} .
- R_{ADC} maximum value is given for $V_{DD}=1.8\text{ V}$, and minimum value for $V_{DD}=3.3\text{ V}$.
- For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in [Table 67](#).

Figure 56. Asynchronous multiplexed PSRAM/NOR read waveforms

Table 77. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_w(NE)$	FSMC_NE low time	$3T_{HCLK}-1$	$3T_{HCLK}+1$	ns
$t_v(NOE_NE)$	FSMC_NEx low to FSMC_NOE low	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_w(NOE)$	FSMC_NOE low time	$T_{HCLK}-1$	$T_{HCLK}+1$	ns
$t_h(NE_NOE)$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_v(A_NE)$	FSMC_NEx low to FSMC_A valid	-	3	ns
$t_v(NADV_NE)$	FSMC_NEx low to FSMC_NADV low	1	2	ns
$t_w(NADV)$	FSMC_NADV low time	$T_{HCLK}-2$	$T_{HCLK}+1$	ns
$t_h(AD_NADV)$	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T_{HCLK}	-	ns
$t_h(A_NOE)$	Address hold time after FSMC_NOE high	$T_{HCLK}-1$	-	ns
$t_h(BL_NOE)$	FSMC_BL time after FSMC_NOE high	0	-	ns
$t_v(BL_NE)$	FSMC_NEx low to FSMC_BL valid	-	2	ns
$t_{su}(Data_NE)$	Data to FSMC_NEx high setup time	$T_{HCLK}+4$	-	ns
$t_{su}(Data_NOE)$	Data to FSMC_NOE high setup time	$T_{HCLK}+4$	-	ns
$t_h(Data_NE)$	Data hold time after FSMC_NEx high	0	-	ns
$t_h(Data_NOE)$	Data hold time after FSMC_NOE high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization.

Table 84. Switching characteristics for PC Card/CF read and write cycles in I/O space⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NIOWR)}$	FSMC_NIOWR low width	$8T_{HCLK} - 1$	-	ns
$t_{v(NIOWR-D)}$	FSMC_NIOWR low to FSMC_D[15:0] valid	-	$5T_{HCLK} - 1$	ns
$t_{h(NIOWR-D)}$	FSMC_NIOWR high to FSMC_D[15:0] invalid	$8T_{HCLK} - 2$	-	ns
$t_{d(NCE4_1-NIOWR)}$	FSMC_NCE4_1 low to FSMC_NIOWR valid	-	$5T_{HCLK} + 2.5$	ns
$t_{h(NCEx-NIOWR)}$	FSMC_NCEx high to FSMC_NIOWR invalid	$5T_{HCLK} - 1.5$	-	ns
$t_{d(NIORD-NCEx)}$	FSMC_NCEx low to FSMC_NIORD valid	-	$5T_{HCLK} + 2$	ns
$t_{h(NCEx-NIORD)}$	FSMC_NCEx high to FSMC_NIORD valid	$5T_{HCLK} - 1.5$	-	ns
$t_{w(NIORD)}$	FSMC_NIORD low width	$8T_{HCLK} - 0.5$	-	ns
$t_{su(D-NIORD)}$	FSMC_D[15:0] valid before FSMC_NIORD high	9	-	ns
$t_{d(NIORD-D)}$	FSMC_D[15:0] valid after FSMC_NIORD high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization.

NAND controller waveforms and timings

[Figure 68](#) through [Figure 71](#) represent synchronous waveforms, and [Table 85](#) and [Table 86](#) provide the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x01;
- COM.FSMC_WaitSetupTime = 0x03;
- COM.FSMC_HoldSetupTime = 0x02;
- COM.FSMC_HiZSetupTime = 0x01;
- ATT.FSMC_SetupTime = 0x01;
- ATT.FSMC_WaitSetupTime = 0x03;
- ATT.FSMC_HoldSetupTime = 0x02;
- ATT.FSMC_HiZSetupTime = 0x01;
- Bank = FSMC_Bank_NAND;
- MemoryDataWidth = FSMC_MemoryDataWidth_16b;
- ECC = FSMC_ECC_Enable;
- ECCPageSize = FSMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 68. NAND controller waveforms for read access

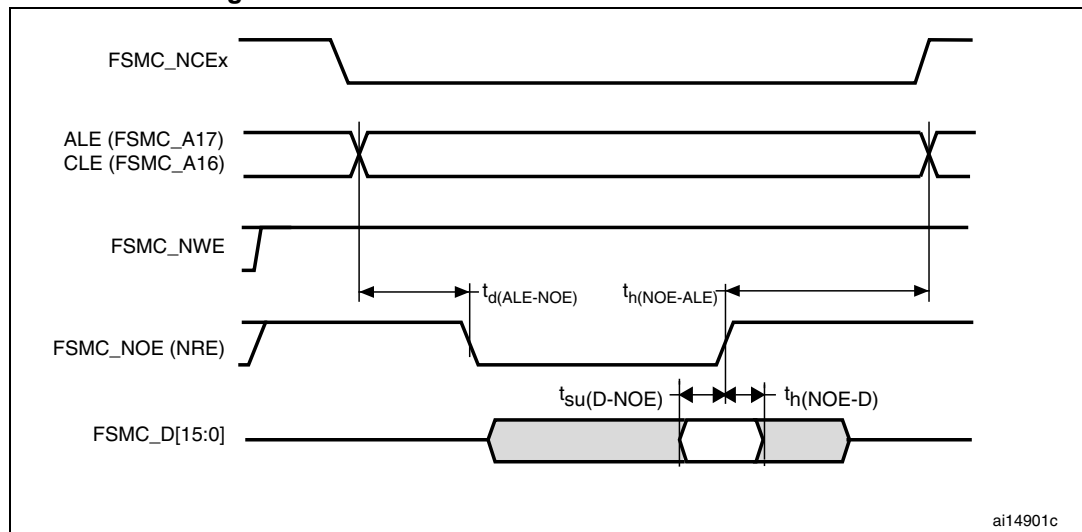
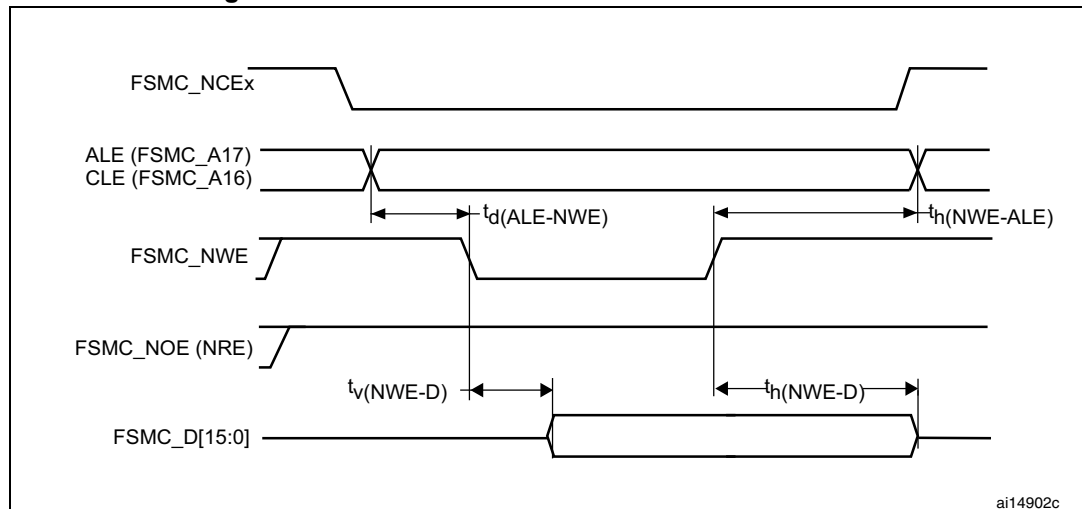
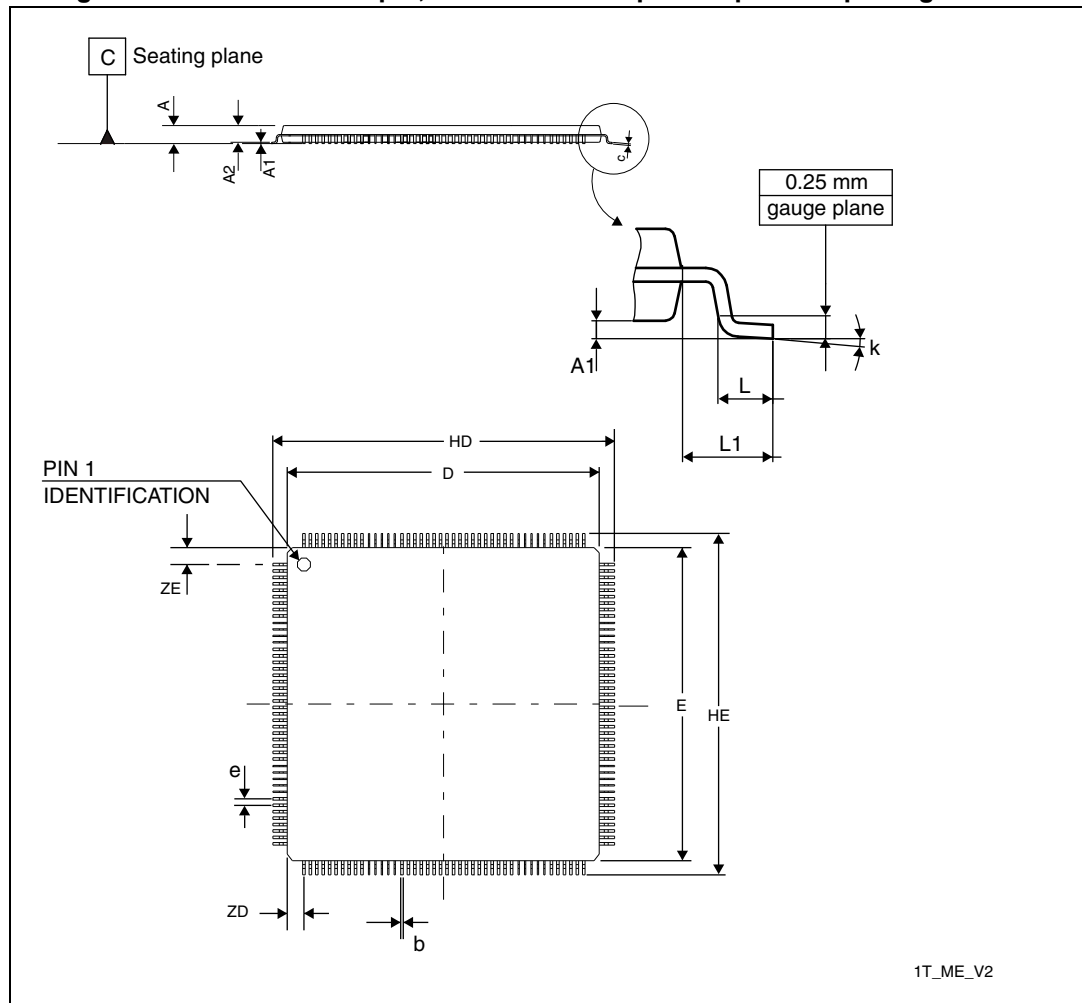


Figure 69. NAND controller waveforms for write access



6.6 LQFP176 package information

Figure 90. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package outline



1. Drawing is not to scale.

Table 97. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488
HD	25.900	-	26.100	1.0197	-	1.0276